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- B21-O-02 *In situ* TEM Observation of Cu-Doped Graphene
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- B21-O-03 The Identification of Grain Boundaries in Two-Dimensional Graphene Using Moire Pattern Fringe
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- B21-O-04 Phase Map of a Single MoS₂ Sheet Retrieved by Aberration Corrected Transport of Intensity Equation
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- B21-O-05 Atomic Motion in Monolayer Molybdenum Disulfide Probed by In-situ ADF-STEM
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 and Chan-Gyung Park^{1,2}.** ¹Department of Material Science and Engineering, Pohang University of Science
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